In-situ real-time and *in-vacuo* study of the temperature impact on the Al_2O_3 ALD nucleation upon pristine monolayer graphene

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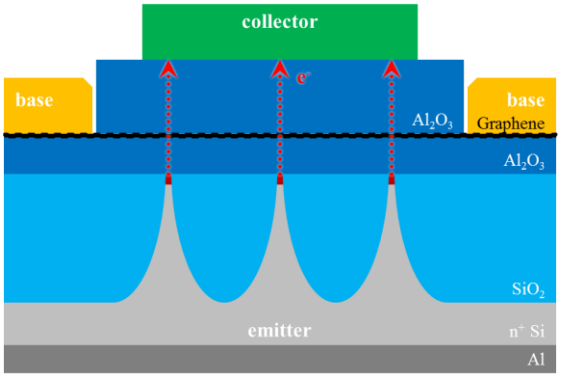
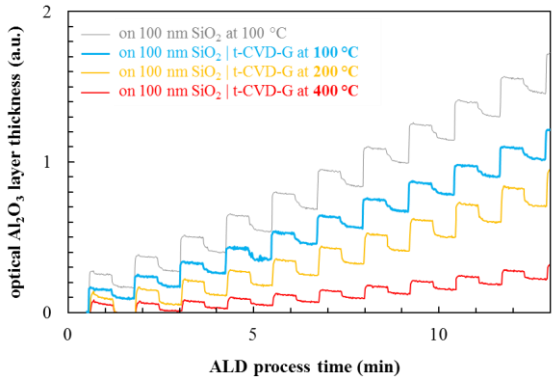
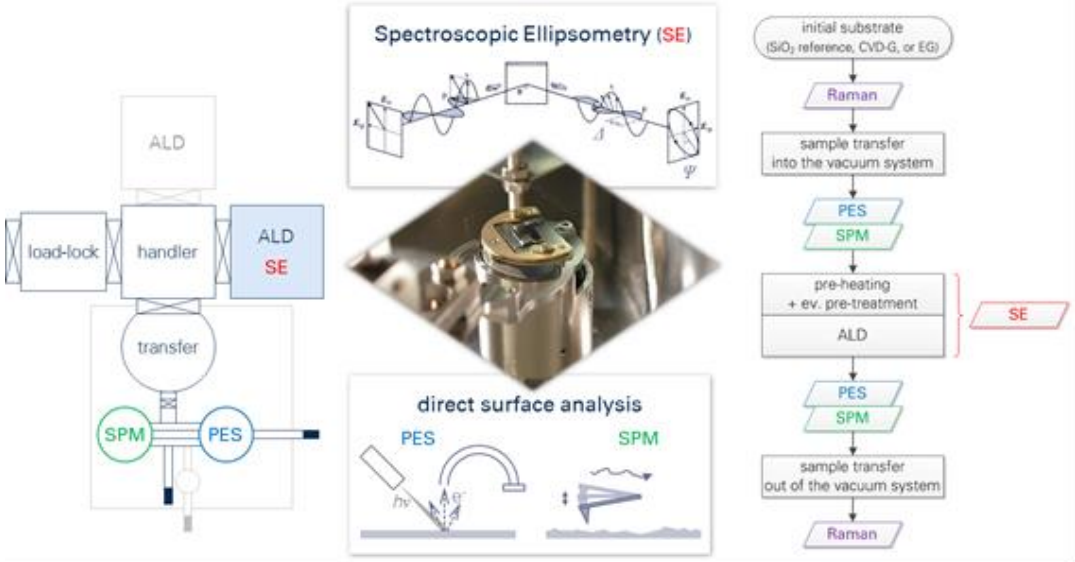
Figures



Schematic concept of a Graphene-Base Transistor.[1]



Al_2O_3 ALD nucleation study by in-situ real-time SE.



Experimental setup and methodology.

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